

■ FEATURES

- Low profile package
- Ideal for automated placement
- Glass passivated chip junction
- High forward surge capability
- Super Fast reverse recovery time
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

■ TYPICAL APPLICATIONS

For use in high frequency rectification of power supplies, inverters, converters, and freewheeling diodes for consumer, and telecommunication.

■ MECHANICAL DATA

- **Package:** SMAF
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** Cathode line denotes the cathode end

■ MAXIMUM RATINGS (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	E2AF	E2BF	E2CF	E2DF	E2FF	E2GF	E2HF	E2JF	E2KF
Device marking code			E2AF	E2BF	E2CF	E2DF	E2FF	E2GF	E2HF	E2JF	E2KF
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	V	50	100	150	200	300	400	500	600	800
Maximum RMS Voltage	V _{RMS}	V	35	70	105	140	210	280	350	420	560
Maximum DC blocking Voltage	V _{DC}	V	50	100	150	200	300	400	500	600	800
Average rectified output current @60Hz sine wave, resistance load, TL (Fig.1)	I _o	A	2.0								
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave, 1 cycle, T _j =25°C	I _{FSM}	A	50								
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, T _j =25°C			100								
Current squared time @1ms≤t≤8.3ms T _j =25°C, Rating of per diode	I ² t	A ² s	10.375								
Typical junction capacitance @Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	C _j	pF	30				16		12		12
Storage temperature	T _{stg}	°C	-55 ~ +150								
Junction temperature	T _j	°C	-55 ~ +150								

■ ELECTRICAL CHARACTERISTICS (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	E2AF	E2BF	E2CF	E2DF	E2FF	E2GF	E2HF	E2JF	E2KF
Maximum instantaneous forward voltage drop per diode	V _F	V	I _{FM} =2.0A	1.0				1.3		1.7		1.85
Maximum reverse recovery time	t _r	ns	I _F =0.5A, I _R =1.0A, I _r =0.25A	35								
Maximum DC reverse current at rated DC blocking voltage per diode	I _R	μA	T _j =25°C	5.0								
			T _j =125°C	100								

■ **THERMAL CHARACTERISTICS** ($T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	E2AF	E2BF	E2CF	E2DF	E2FF	E2GF	E2HF	E2JF
Typical Thermal resistance	$R_{\theta J-A}^{(1)}$	$^\circ\text{C/W}$	75							
	$R_{\theta J-L}^{(1)}$		25							
	$R_{\theta J-C}^{(1)}$		20							

Note:
(1) Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas

■ **CHARACTERISTICS (TYPICAL)**

FIG1: I_o -TL Curve

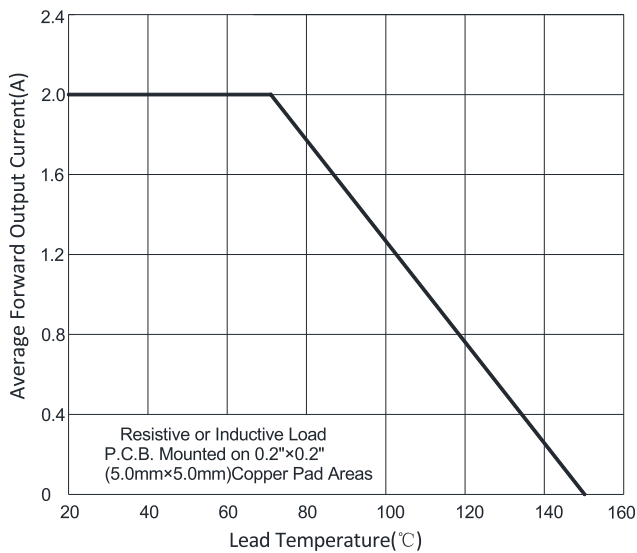


FIG2: Surge Forward Current Capability

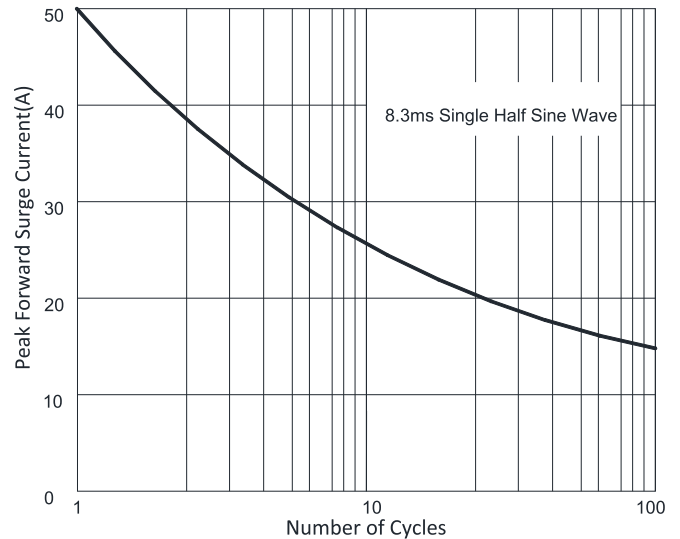


FIG3: Typical Forward Voltage

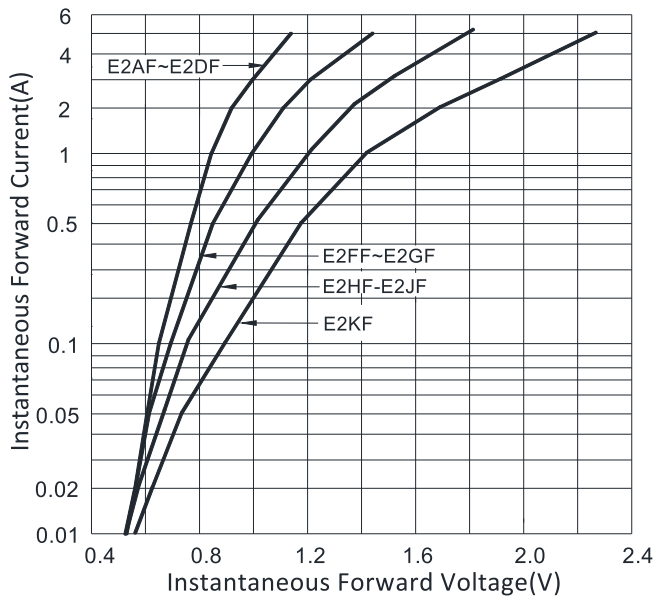


FIG4: Typical Reverse Characteristics

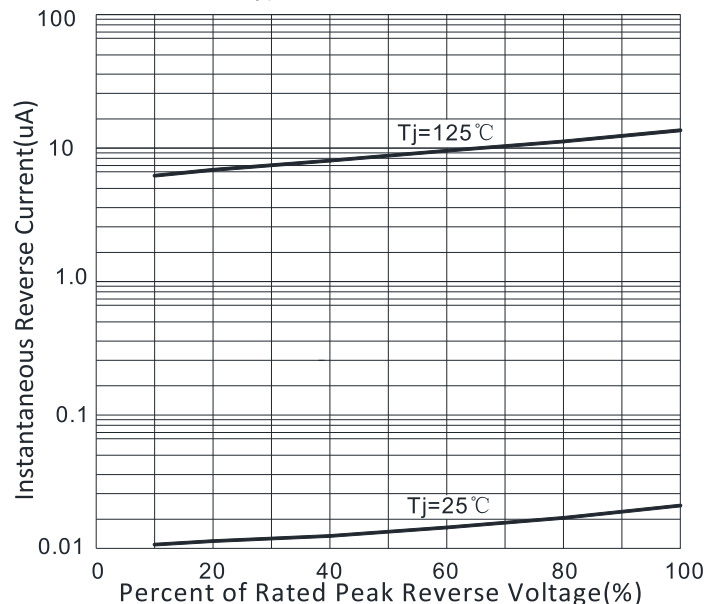
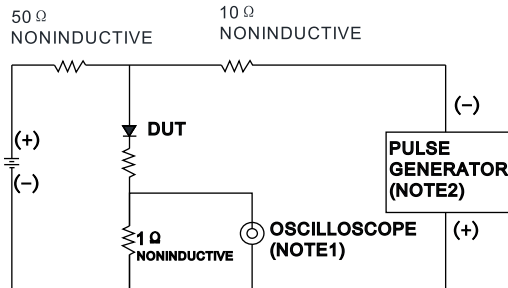
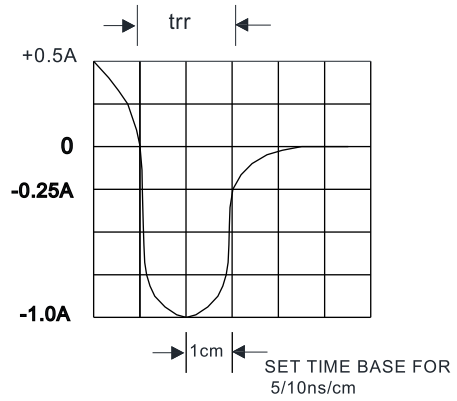


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time



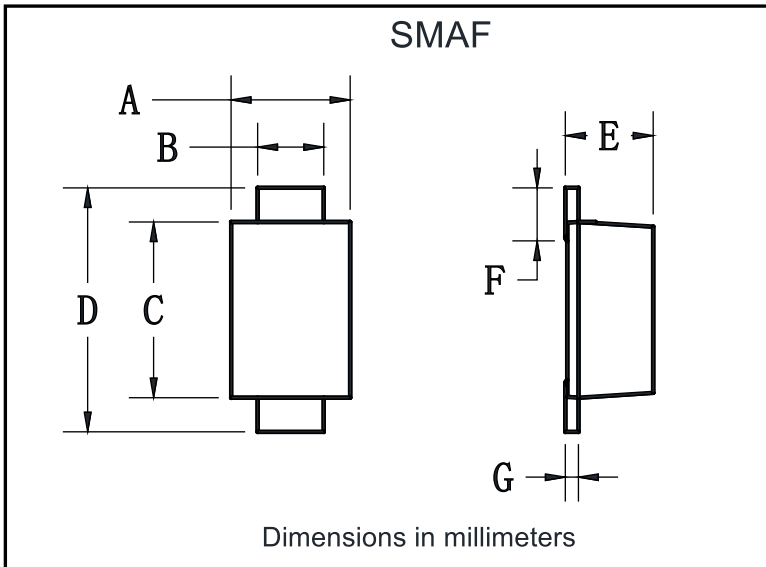
NOTES:
1. Rise Time=7ns max .Input Impedance=1M Ω 22pf
2. Rise Time=10ns max. Source Impedance=50 Ω



■ **PACKAGING INFORMATION**

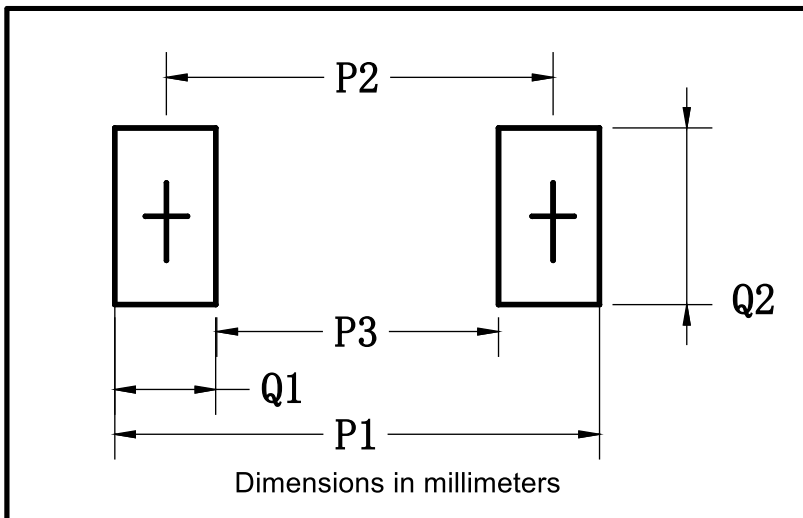
PREFERED P/N	PACKING CODE	UNIT WEIGHT(g)	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
E2AF-E2KF	F1	Approximate 0.034	3000	24000	96000	7" reel
E2AF-E2KF	F2	Approximate 0.034	10000	20000	160000	13" reel
E2AF-E2KF	F3	Approximate 0.034	10000	20000	120000	13" reel
E2AF-E2KF	F4	Approximate 0.034	7500	15000	120000	13" reel

■ **OUTLINE DIMENSIONS**



SMAF		
Dim	Min	Max
A	2.40	2.80
B	1.35	1.45
C	3.40	3.60
D	4.40	4.80
E	1.05	1.25
F	0.50	1.00
G	0.15	0.22

■ **SUGGESTED PAD LAYOUT**



SMAF	
Dim	Millimeters
P1	6.50
P2	4.00
P3	1.50
Q1	2.50
Q2	1.70